

### Description

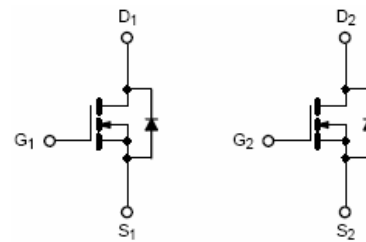
The 9926 uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

### General Features

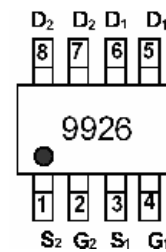
- |           |                             |                             |       |
|-----------|-----------------------------|-----------------------------|-------|
| $V_{DSS}$ | $R_{DS(ON)}$<br>@4.5V (Typ) | $R_{DS(ON)}$<br>@2.5V (Typ) | $I_D$ |
| 20V       | 16m $\Omega$                | 20 m $\Omega$               | 6A    |
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- RoHS Compliant

### Application

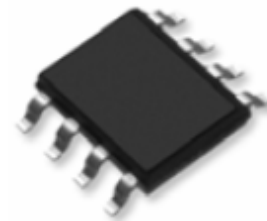
- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



Schematic diagram



Marking and pin Assignment



SOP-8

### Ordering Information

Part Number	Marking	Case	Packaging
9926	9926	SOP-8	4000pcs/Reel

### Absolute Maximum Ratings (TC=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	±10	V
Drain Current-Continuous	$I_D$	6	A
Drain Current-Continuous( $T_C=100^\circ\text{C}$ )	$I_D(100^\circ\text{C})$	3.8	A
Pulsed Drain Current	$I_{DM}$	25	A
Maximum Power Dissipation	$P_D$	1.25	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 150	°C

### Thermal Characteristic

Thermal Resistance, Junction-to-Ambient(Note 2)	$R_{\theta JA}$	100	°C/W
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**Electrical Characteristics (TC=25°C unless otherwise noted)**

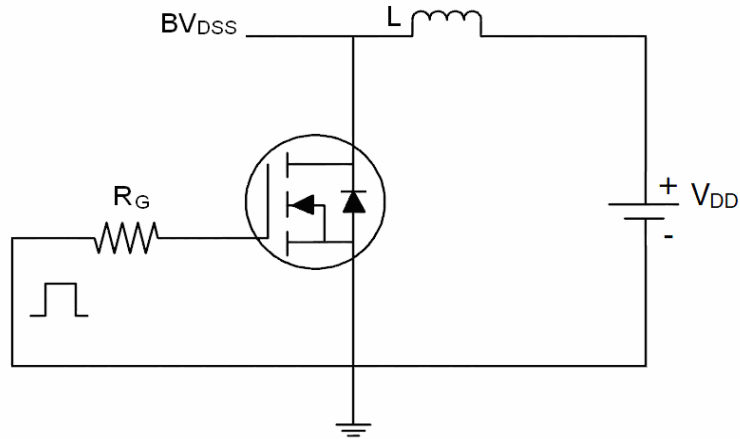
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Off Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	20	22	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=20V, V_{GS}=0V$	-	-	1	$\mu A$
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 8V, V_{DS}=0V$	-	-	$\pm 100$	nA
<b>On Characteristics (Note 3)</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	0.5	-	1.2	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=4.5V, I_D=4.5A$	-	16	25	m $\Omega$
		$V_{GS}=2.5V, I_D=4A$	-	20	30	
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=6A$	20	-	-	S
<b>Dynamic Characteristics (Note4)</b>						
Input Capacitance	$C_{iss}$	$V_{DS}=10V, V_{GS}=0V,$ $F=1.0MHz$	-	640	-	PF
Output Capacitance	$C_{oss}$		-	140	-	PF
Reverse Transfer Capacitance	$C_{rss}$		-	80	-	PF
<b>Switching Characteristics (Note 4)</b>						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=10V, I_D=1A$ $V_{GEN}=4.5V, R_G=6\Omega$	-	8	-	nS
Turn-on Rise Time	$t_r$		-	9	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	15	-	nS
Turn-Off Fall Time	$t_f$		-	4	-	nS
Total Gate Charge	$Q_g$	$V_{DS}=10V, I_D=3A,$ $V_{GS}=4.5V$	-	10	-	nC
Gate-Source Charge	$Q_{gs}$		-	1.5	-	nC
Gate-Drain Charge	$Q_{gd}$		-	1.6	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	$V_{SD}$	$V_{GS}=0V, I_S=1.7A$	-	-	1.15	V
Diode Forward Current (Note 2)	$I_S$		-	-	6	A

**Notes:**

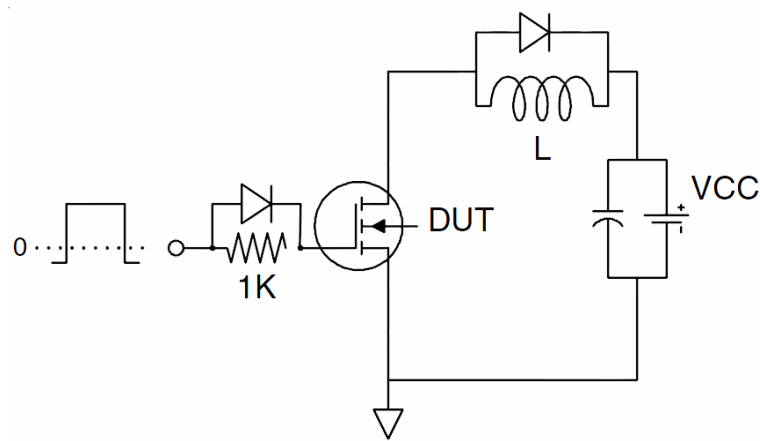
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production

**Test Circuit**

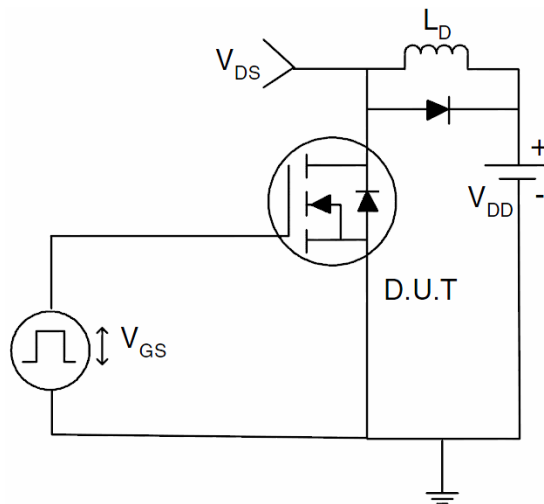
**1) E<sub>AS</sub> Test Circuits**



**2) Gate Charge Test Circuit:**



**3) Switch Time Test Circuit:**



Typical Electrical and Thermal Characteristics (Curves)

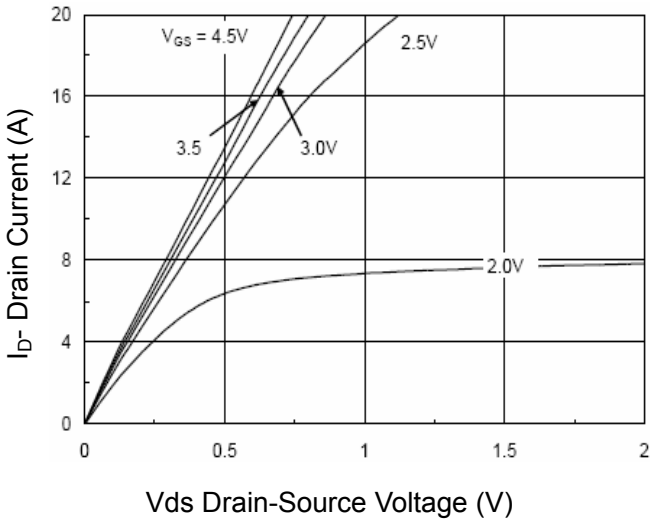


Figure 1 Output Characteristics

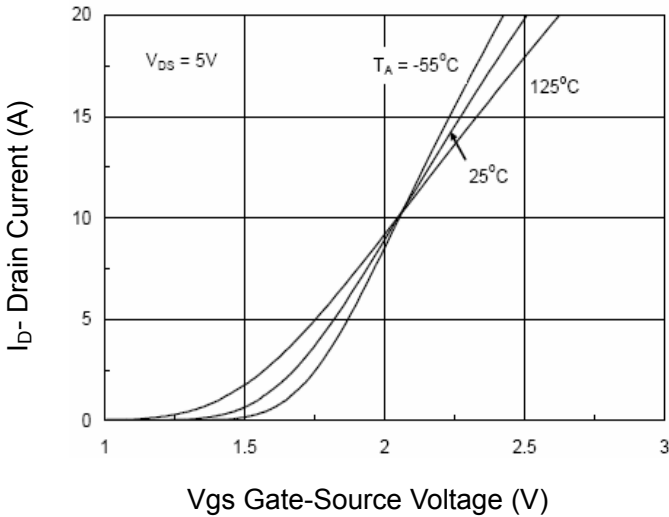


Figure 2 Transfer Characteristics

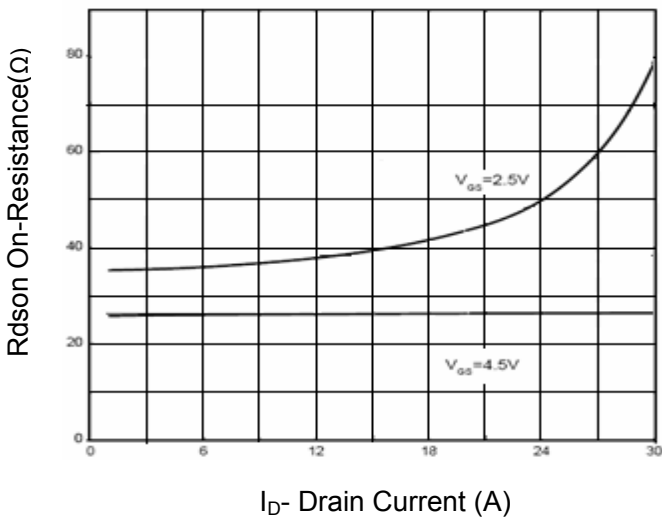


Figure 3 Rdson- Drain Current

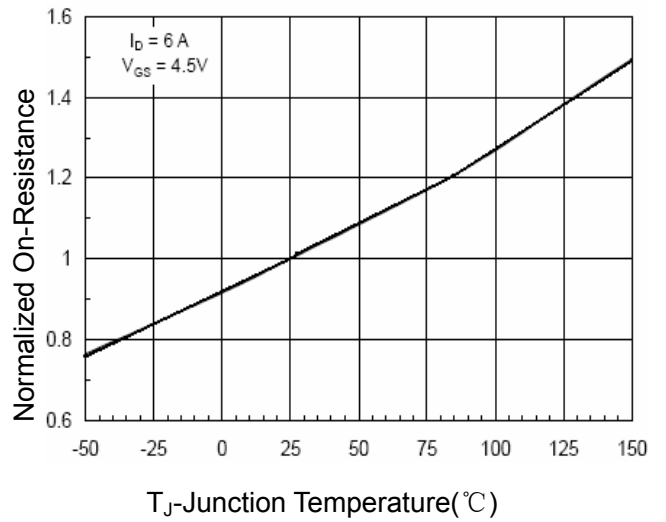


Figure 4 Rdson-Junction Temperature

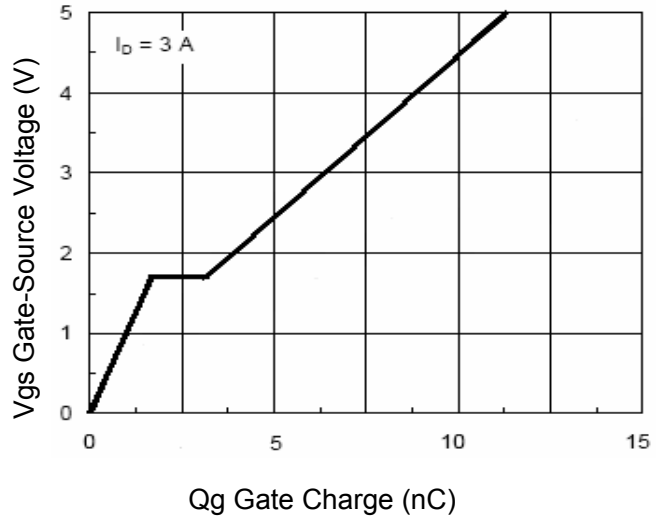


Figure 5 Gate Charge

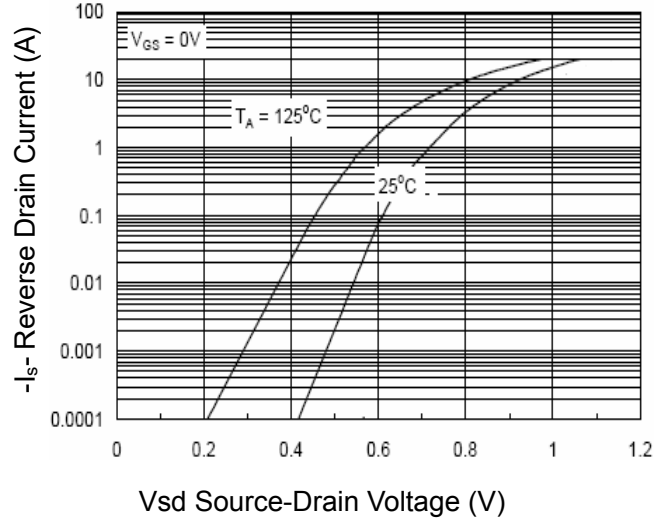
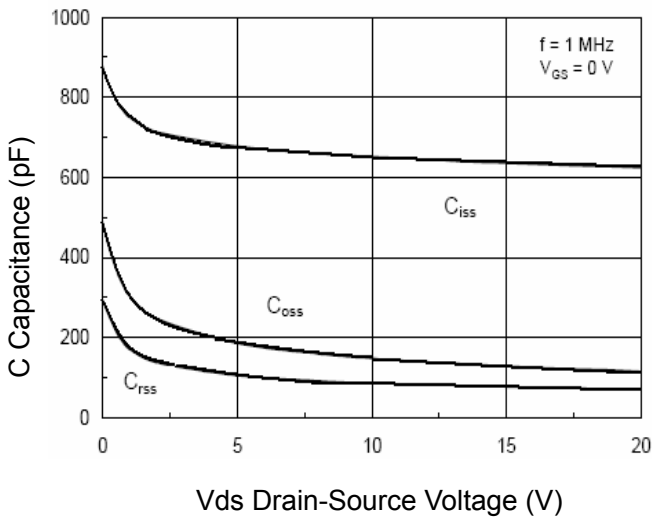
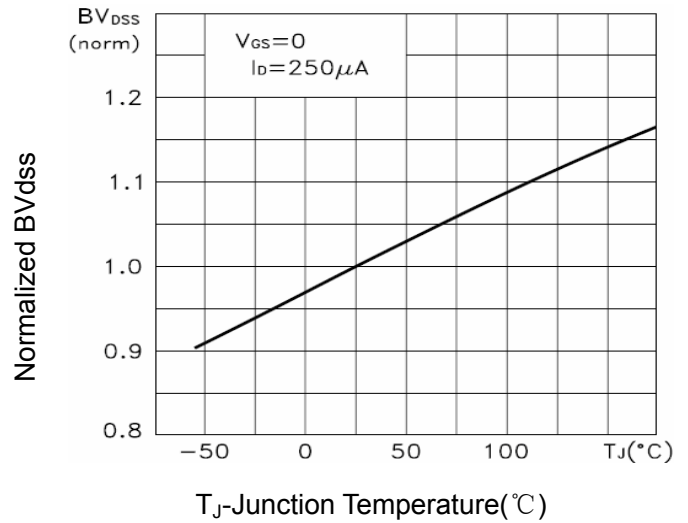


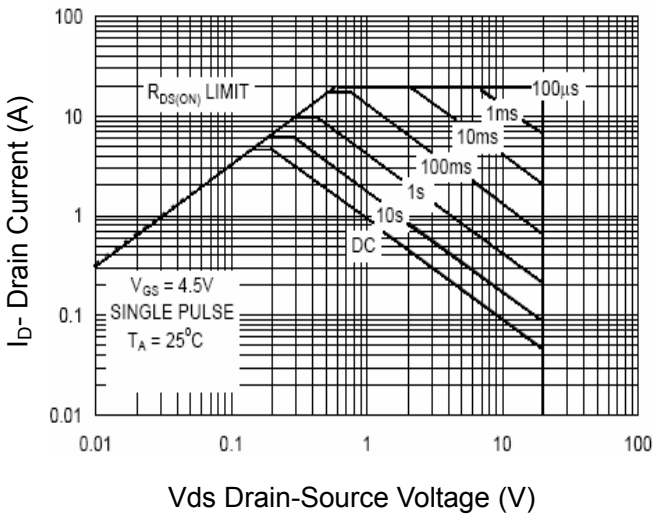
Figure 6 Source- Drain Diode Forward



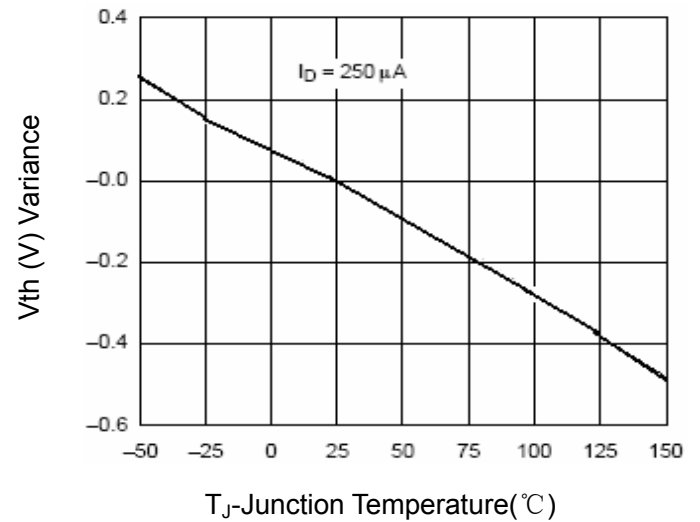
Vds Drain-Source Voltage (V)  
**Figure 7 Capacitance vs Vds**



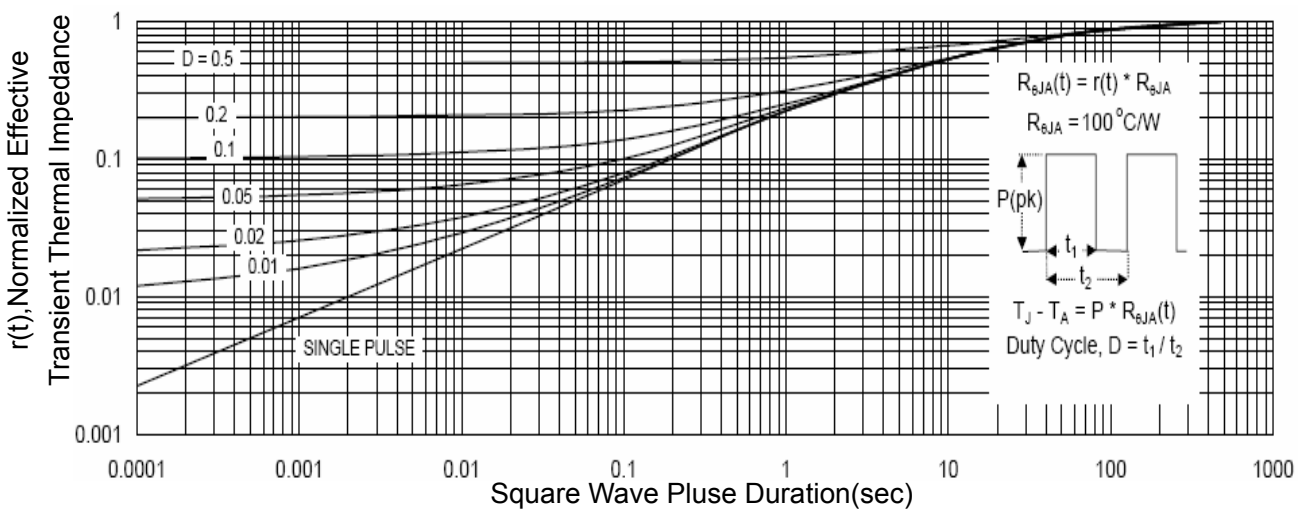
T<sub>J</sub>-Junction Temperature(°C)  
**Figure 9 BV<sub>DSS</sub> vs Junction Temperature**



Vds Drain-Source Voltage (V)  
**Figure 8 Safe Operation Area**

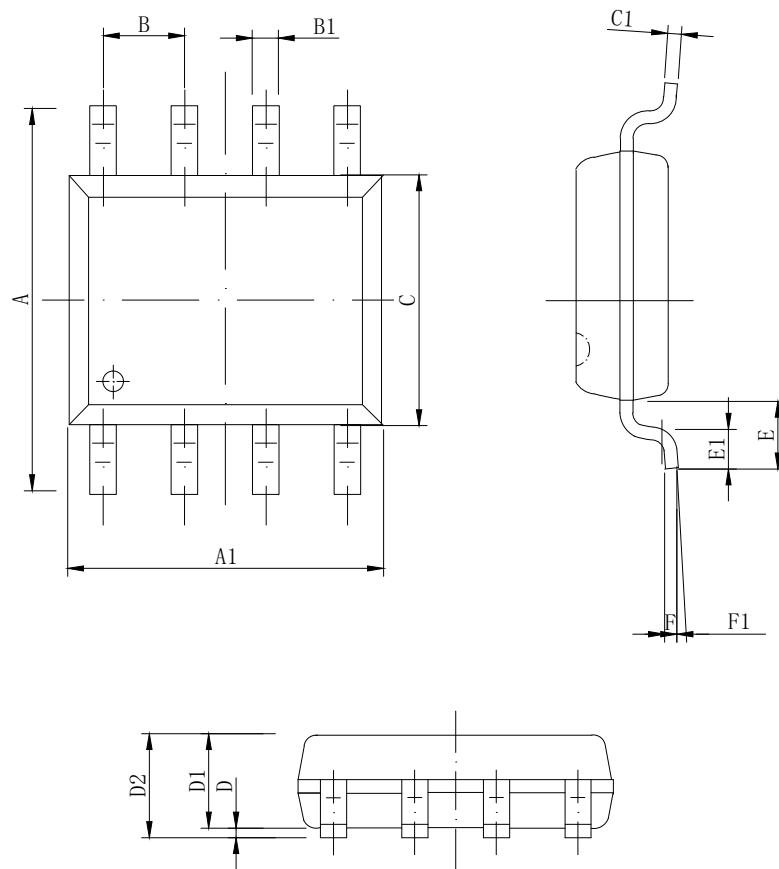


T<sub>J</sub>-Junction Temperature(°C)  
**Figure 10 V<sub>GS(th)</sub> vs Junction Temperature**



**Figure 11 Normalized Maximum Transient Thermal Impedance**

SOP-8 Package information



DIM	MIN	NOM	MAX
A	5.800	6.000	6.200
A1	4.800	4.900	5.000
B	1.270BSC		
B1	0.35 ^ 8x	0.40 ^ 8x	0.45 ^ 8x
C	3.780	3.880	3.980
C1	-	0.203	0.253
D	0.050	0.150	0.250
D1	1.350	1.450	1.550
D2	1.500	1.600	1.700
E	1.060 REF		
E1	0.400	0.700	0.100
F	0.250BSC		
F1	2°	4°	6°

All Dimensions in mm